YJ Planar Schottky Barrier Diode Die Specification

200V 20A, 102mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB102H200AS-280A

Main Products Characterstics

- Average forward current: IF(AV) = 20 A
- Maximum operating junction temperature: Tj = 175 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL

Maximum Ratings

Non−repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	150 A
Maximum operating junction		

Static Electrical Characteristics (Ta = 25°C)

		Value	
		Spec	**Typical**
		210 V	230V
Maximum forward voltage drop			
I_F = 20 A	V_F	0.92V	0.88V
Pulse Test: tp = 300 μs, δ 2%			
Max		3uA	0.3uA

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	2*48.6*98 Mils
Active Area	2*43.8*93.4 Mils
Space between die	0.98 Mils
Top Metal	AL
Back Metal	Ag

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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